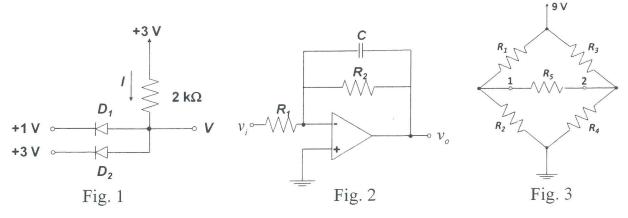
國立臺灣師範大學101學年度碩士班招生考試試題

科目:電子學 適用系所:光電科技研究所

注意:1.本試題共 2 頁,請依序在答案卷上作答,並標明題號,不必抄題。2答案必須寫在指定作答區內,否則依規定扣分。

第 1~6 題選擇題,無需計算過程,第 7~13 題為計算作圖題,必需運算過程及完整繪圖

- 1. For the circuit shown in Fig. 1 using ideal diodes, find the values of I and V(1) I = 0 mA, V = 0 V (2) I = 1 mA, V = 1 V (3) I = 2 mA, V = 2 V (4) I = 3 mA, V = 3 V (5) unknown (5 $\frac{1}{2}$)
- 2. For the circuit shown in Fig. 2, $R_1 = 1$ kΩ, voltage gain 50, band width $\omega_{3dB} = 10^4$ rad/s, please find $R_2 = (1)$ 0.01 kΩ (2) 0.02 kΩ (3) 1 kΩ (4) 50 kΩ (5) 100 kΩ (5 $\frac{1}{2}$)
- 3. Continue question 2, in Fig. 2, please find $C = (1) 10 \mu F (2) 5 \mu F (3) 100 nF (4) 2 nF (5) 1 nF (5 <math>\%$)
- 4. The definition of CMRR (common-mode rejection ratio) is (1) A_c/A_d (2) A_d/A_c (3) V_c/V_d (4) V_d/V_c (5 %)
- 5. For Field Effect Transistors (FETs), choose the wrong statement(s)? (1) The gate current, $I_G=0$ (2) There are JFET, depletion-type MOSFET, and enhancement -type MOSFET (3) The drain current I_D is determined by V_G (gate voltage) (4) I_D is determined by I_G (5) $I_G=\infty$ (5 %)
- 6. The emitter, base, and collector voltages of an *npn* transistor are -0.7 V, 0 V, and -0.6 V, respectively. Please identify the mode of operation of the transistor. (1) active (2) saturation (3) inverted (4) cut off (5 分)
- 7. The circuit shown in Fig. 3 represents the equivalent circuit of an unbalanced bridge. Note $R_1 = 1 \text{ k}\Omega$, $R_2 = 1.2 \text{ k}\Omega$, $R_3 = 9.1 \text{ k}\Omega$, $R_4 = 11 \text{ k}\Omega$, and $R_5 = 3 \text{ k}\Omega$. It is required to calculate the current in the detector branch (R_5) and the voltage across it. Although this can be done using loop and node equations, a much easier approach is possible: Find the Thevenin equivalent of the circuit to the left of node 1 and the Thevenin equivalent of the circuit to the right of node 2. Then solve the resulting simplified circuit. (10 %)



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- 8. Please draw the small-signal Model equivalent-circuit of MOSFET including body effect. (10 分)
- 9. The circuit in Fig. 4 is frequently used to provide an output voltage v_o proportional to the input signal current i_i . Derive expressions for the transresistance $R_m \equiv v_o/i_i$, and the input resistance $R_i \equiv v_i/i_i$ for the following cases: (a) A is infinite. (b) A is finite. (10 %)
- 10. The FET-input OP AMP gives an output of 0.5 V when connected as shown in Fig. 5 ($R_I = 100~\Omega$, $R_2 = 33~\mathrm{k}\Omega$) (a) What is the input offset voltage, V_{os} ? (b) Now, R_I is changed to 50 k Ω , R_2 is replaced by a 1 nF capacitor, find V_o as a function of t. ($V_o(t=0) = 0$ V, and $V_{osat} = \pm 13$ V) (10 %)
- 11. A BJT for which BV_{CBO} is 30 V is connected as shown in Fig. 6. What voltages would you measure on the collector, base, and emitter? (10 %)
- 12. Can two back-to-back connected p-n junction diodes be used as a transistor? Why? (10 分)
- 13. Consider the storage capacitor for panel display application $\sim \exp(-t/RC)$, t is time. Assume the $\varepsilon_{LC} \times \varepsilon_0 = 7 \times 8.85 \times 10^{-14}$ F/cm, and the initial voltage is 3 V. Please calculate the voltage after 16.67 ms (60Hz refresh rate) with (a) the resistance of liquid crystal $\sim 10^{11} \Omega$ -cm, (b) the resistance of liquid crystal $\sim 10^{13} \Omega$ -cm for currently process. (10 \Re)

